SPECIFICATION

Device Name

IGBT-IPM

Type Name

6MBP15RY060

Spec. No.

MS6M0362

Fuji Electric Co.,Ltd. Matsumoto Factory

DATE NAME APPROVED

DRAWN 5.1. 13. '98 (Nichrate)

O-ED-ED 5.1. 13. '98 (Nichrate)

S. Kebeyashi

H04-004-07

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Revised Record

Applied Content Drawn Checked Date Classification Ind. Approved Date issued Enactment Date Addition, packing spec. 1/1, Sep. - 29 zep.-29 α Revision 198 Resission, at time 3/11 - 98 Raision. Toc Addition, plating space Correction, smorts in uniting Nov. - 10 NOV. 10 Revision - 198 Revision Isize of packing box Feb->3 Feb-23 Revision C - 99 199 Correction : Briefs in writing

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3. Maximum Ratings (最大定格)

(Tc=25°C unless otherwise specified)

Items		Symbols	Ratings	Unit
DC Bus Voltage		VDC	450	\ \ \
DC Bus Voltage (surge) DC Bus Voltage (short operating) Collector-Emitter Voltage		VDC(surge)	500	٧
		Vsc	400	٧
		VCES	600	V
Collector Current	DC	IC	15	Α
	1ms	ICP	30	А
	Duty=44.1%	-lc	15	Α
Collector Power Dissipation	Collector Power Dissipation One Transistor		40	Ŵ
Junction Temperature		Tj	_150	°C
Input Voltage of Power Supply fo	r Pre-Driver	Vcc	-0.3~20_	V
Input Signal Current		lin	20	mA
Alarm Signal Voltage		VALM	Vcc	V
Alarm Signal Current		IALM	15	mA
Storage Temperature		Tstg	-40~125	ဇ
Operating Case Temperature		Тсор	-20~100	°C
Isolating Voltage (Terminal to base,50/60Hz sine wave 1min.)		Viso	AC 2500	V
Screw Torque		Mounting (M4)	2.0	N·m

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4.1 Electrical Characteristics of Power Circuit (主回路部電気的特性)

(Tj=Tc=25°C, Vcc=15V)

Items	Symbols	Conditions	min.	typ.	max.	Unit
Collector Current at off Signal Input	ICES	VCE=600V, lin=0mA	-	-	1.0	mA
Collector-Emitter Saturation Voltage	VCE(sat)	IC=15A, lin=10mA	-	-	2.7	٧
Forward Voltage of FWD	VF	-IC=15A, lin=0mA	_	-	3.5	٧

4.2 Electrical Characteristics of Control Circuit (制御部電気的特性)

(Tj=Tc=25°C, Vcc=15V)

			(1)-1	c=25 C,	ACC-19	v)	
ltems	Symbols	- Conditions	min.	typ.	max.	Unit	
Power Supply Current of P-line Pre-driver (one unit)	ICCP	lin=0mA,	-	2.0	5.0	mA	
Power Supply Current of N-line Pre-driver	ICCN	lin=0mA,	_	4.0	10.0	mA	
Input Signal Threshold Current	lin(th)	Turn-on	-	1.8	2.3	mA	
		Turn-off	0.8	1.3	-	mA	
Hysteresis of Input Signal Theshold Current	linH	-	-	0.5	-	mA	
Input Signal Saturation Voltage	Vin(sat)	lin=20mA		0.8	2.0	V	
Over Heating Protection(過熱保護)							
IGBT chips Over HeatProtection Temperature Level	Тјон	Surface of IGBT	150	-	-	°C	
Hysteresis	Тјн	-	-	20	_	°C	
Over Current Protection(過電流保証	菱)						
Collector Current Protection Level	loc	N-side, (N1-N2 open)	18	22	26	Α	(b)
	Voc	Between N1 and N2	190	200	210	mV	
OC detecting resistance value	Roc		-	9.0	-	mΩ	
Protection Delay time	tDOC	Tj=25°C Fig. 1, Fig. 2	_	5.0	7.0	μs	
Power Supply Under Voltage Protection	on(電源電圧	低下保護)					
Under Voltage Protection Level	Vuv	-	11.0	_	12.5	V	
Hysteresis	VH	-	0.2	-	0.8	V	
Alarm Signal Output (アラーム信号出	カ)						
Alarm Signal Hold Time	tALM	-	1.0	2.0	_	ms	
							- 1

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5. Switching Characteristics (スイッチング特性)

(Tj=Tc=25°C, Vcc=15V)

ltems	Symbols	Conditions	min.	typ.	max.	Unit
Switching Time (IGBT)	ton	lc=15A, VDC=300V	0.5	-	-	μs
	toff	lin=10mA	-	-	5.0	μs
Switching Time (FWD)	trr	Inductive-Load, Fig. 3	_	_	0.5	μs

6. Thermal Characteristics (熱特性)

(Tj=Tc=25°C, Vcc=15V)

Items		Symbols	min.	typ.	max.	Unit
Junction to Case Thermal Resistance	IGBT	Rth(j-c)	_	-	3.1	°C/W
	FWD	Rth(j-c)	-	-	5.4	°C/W
Case to Fin Thermal Resistance with Compound		Rth(c-f)	-	0.05	_	°C/W

7. Recommendable Value (推奨値)

Items	Symbols	Conditions	min.	typ.	max.	Unit
DC Bus Voltage	VDC	-	200	-	400	V
Operating Power SupplyVoltage Range of Pre-drive	Vcc	-	13.5	15	16.5	٧
Input Signal Current	lF	CTR=100~200%	8	-	10	mA
Switching Frequency	fsw	-	1	3	5	kHz
Flatness of heat sink		-	-100	_	100	μm
Mounting Screw Torque (M4)		-	1.3	-	1.7	N·m

8. Weight (重量)

ltems	Symbols	Conditions	min.	typ.	max.	Unit
Weight	-	-	_	50	ı	g

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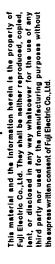
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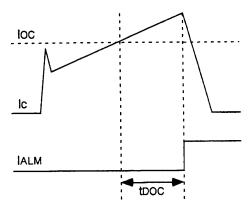


Fig. 1. Definition of OC protection delay time (過電流保護遅れ時間の定義)

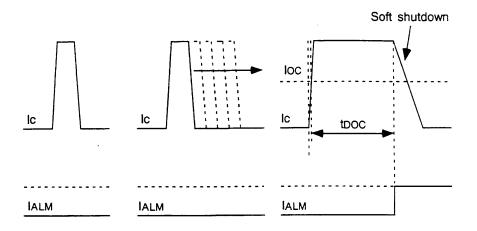


Fig. 2. Definition of protection delay time at short circuit (短絡時保護遅れ時間の定義)

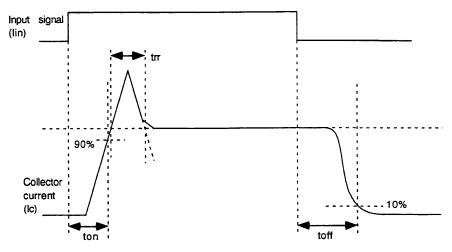
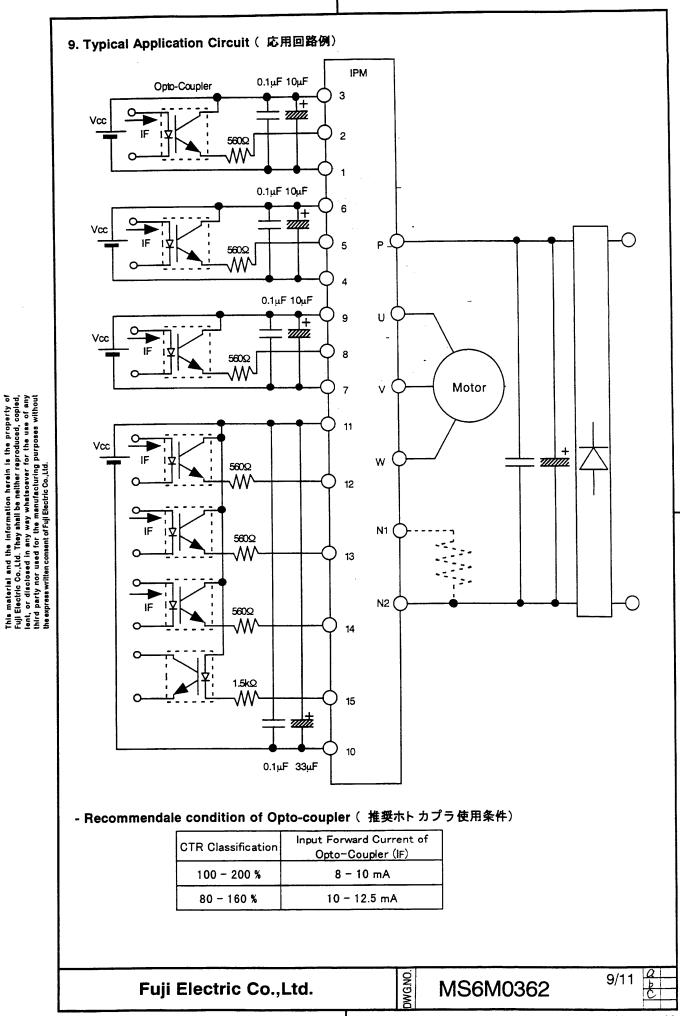


Fig. 3. Definition of switching time (スイッチング時間の定義)



10. Application Guideline (適用時の注意事項)

- The wiring between the opto-couplers and the input terminals of the IPM should be as short as possible. The stray capacitance between primary and secondary side of the opto-couplers should not be increased by pattern lay-out of the control circuits.

フォトカプラと PMの入力端子間配線はできるだけ短くし、フォトカプラの1次・2次間の浮遊 容量を増加させないパターンレイアウトとしてください。

- Capacitors should be connected between Vcc and GND terminals of the opto-coupler as closely as possible.

フォトカプラのV∞-GND間には、コンデンサをできるだけ近接して取り付けてください。

- Each power supplies for drive circuits should not have transient voltage fluctuation. Four power supplies which are isolated should be applied individually.

各制御電源は瞬時電圧変動の少ない、絶縁されたものを4個独立に使用してください。

- In order to prevent noise from AC line, connect capacitor (approx. 4.7nF) between three-phase line and earth.

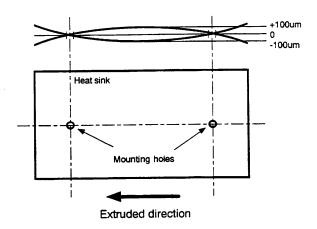
ACラインからのノイズの侵入を防ぐため、3 相各線—アース間に4.7nF程度のコンデンサを接続してください。

- Do not connect N2-terminal of main circuit to ground (GND) of the control circuit. 入力回路のグランド (GND)と主回路N2端子を接続しないでください。

11. Heat sink mounting precautions (I P Mの取り付け方法)

- A mounting surface of a heat sink should be finished to a roughness below $10\mu m$ and a flatness between screw holes below $100\mu m$. If the flatness is below $-100\mu m$, a thermal resistance between an IPM and a heat sink is increased. If the flatness is over $+100\mu m$, there is the danger of the isolation failure.
- I P Mを取り付けるヒートシンク面の仕上げは、粗さ10μm以下、ネジ位置間での面の平坦度 (反り) 100μm以内にして下さい。平坦度が-100μm以下の場合、ヒートシンクへの接触熱抵抗が増加します。また、平坦度が+100μm以上の場合、絶縁破壊を起こす危険性があります。
- Apply a thermal compound between an IPM and a heat sink to reduce a contact thermal resistance. 接触熱抵抗を小さく するために、IPMとヒートシンクの間にサーマルコンパウンドを塗布して下さい。
- Mount an IPM in parallel with extruded direction of a heat sink to reduce an influence of a change of a heat sink, when a heat sink which is made by an extruder is applied.

押し出し機によって作られたヒートシンクを使用する場合は、ヒートシンクの変形の影響を小さくするためにIPMをヒートシンクの押し出し方向と平行に取り付けて下さい。

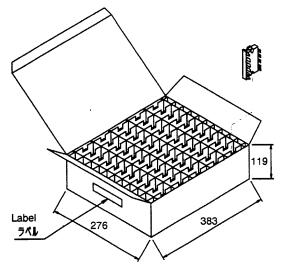


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12. Packing and indication (梱包と表示) (C)



Material : Corrugated cardbord

材料 ダンボール

Weight: Approx. 3.1kg (max.)

重量 約3.1kg (最大)
Quantity : 50pcs (max.)
数量 50個 (最大)



13. Storage and transportation notes (保管、運搬上の注意事項)

- The IGBT-IPM should be stored at a standard temperature of 5 to 35℃ and humidity of 45 to 75%. 室内で常温常湿保存が望ましい。(5 ~3 5 ℃、4 5 ~7 5 %)

- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.

急激な温度変化がないこと。(モジュール表面が結露しないこと)

- Avoid exposure to corrosive gases and dust.

腐食性ガスの発生場所、塵埃の多い場所は避けること。

- Avoid excessive external force on the modules.

半導体製品に荷重がかからないように注意すること。

- Store modules with unprocessed terminals.

モジュールの端子は未加工の状態で保管すること。

- Don't drop and shock the modules during transportation.

運搬時に衝撃を与えたり落下させないこと。

14. Operation environment (使用環境)

- Avoid exposure to corrosive gases. 腐食性ガスの雰囲気での使用は避けること。

15. Applicable category (適用範囲)

- This specification is applied to the IGBT-IPM named 6MBP15RY060. 本仕様書は、IGBT-IPM(型式: 6MBP15RY060) に適用する。

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